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1 Introduction

Magnetic field sensors are essential in applications such as automotive systems, industrial automation, and biomedical devices. Among these, planar Hall effect (PHE) sensors are notable for their high sensitivity (EMN in the pT/VHz range), simple design, and compatibility with integrated circuits. However, their field range is typically limited to hundreds of μT , restricting their use in applications requiring broader field ranges.

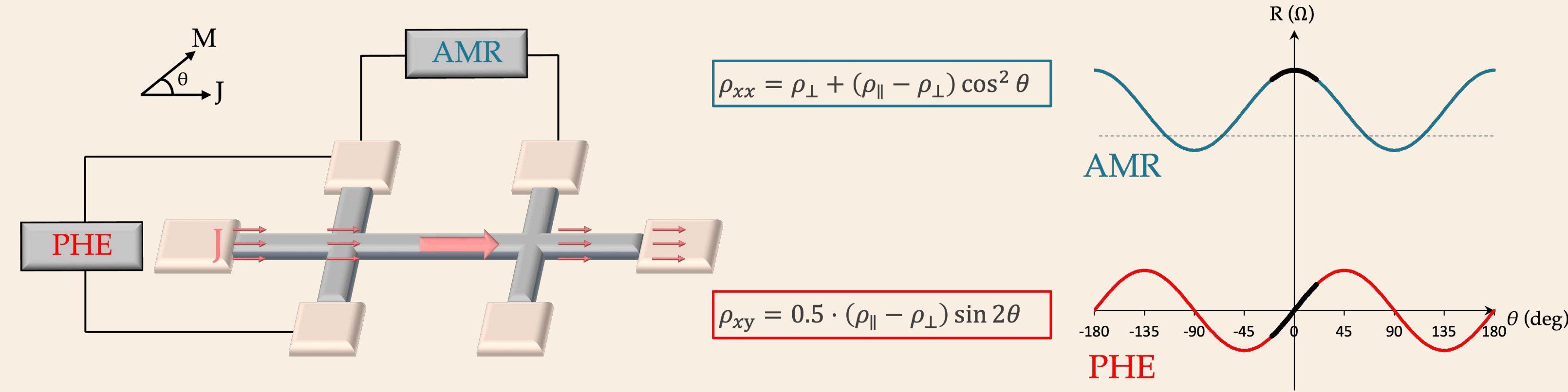
To overcome this limitation, we manipulated the shape-induced anisotropy in elliptical PHE (EPHE) sensors by tailoring their geometry while maintaining consistent film thickness. This approach achieved a tenfold increase in the anisotropy field, extending the field range from sub-mT to tens of mT. These EPHE sensors exhibit stable performance with minimal hysteresis, making them promising for precise magnetic sensing in demanding industrial and scientific applications.

2 Principle and Design

Magnetoresistance

Ferromagnetic materials exhibit a phenomenon called anisotropic magnetoresistance (AMR), in which their resistance changes depending on the orientation of their magnetization ($\mathbf{M}$) relative to the direction of an applied electric current density ($\mathbf{J}$).

This phenomenon gives rise to a transverse voltage as a function of the angle θ between $\mathbf{M}$ and $\mathbf{J}$. This effect is called PHE as the magnetization, the electric current, and the transverse electric field are in the same plane.



Planar Hall Effect Sensors

PHE sensors detect magnetic fields by measuring the transverse voltage, which depends on the angle between magnetization and current. Uniform magnetization with reversible behavior, ensured by aligning magnetic anisotropy parallel to the current, is essential for optimal performance.

Elliptical Planar Hall Effect Sensors

The elliptical shape of PHE sensors induces uniaxial 'shape anisotropy' along the long axis, referred to as the easy axis (EA). For a flat ellipsoid with thickness t , major axis a , and minor axis b , the anisotropy field is:

$$H_s \sim 4\pi M_s \frac{t}{b} \sim 10807 \frac{t}{b}$$

Sensitivity

The sensitivity (S_y) of a PHE sensor is the ratio of its PHE voltage (V_y) to the applied magnetic field in the y-direction (H_y), for a given current (I_x) along the easy axis.

$$S_y = \frac{V_y}{H_y} = I_x \frac{\Delta\rho}{t} \frac{1}{H_s + H_g} = I_x \frac{\Delta\rho}{t} \frac{1}{H_{\text{eff}}}$$

Excitation current I_x , Sensor thickness t , Growth anisotropy H_g , Shape anisotropy H_s , Resistivity anisotropy $\Delta\rho = (\rho_{\parallel} - \rho_{\perp})$.

Equivalent Magnetic Noise (EMN)

The equivalent magnetic noise of the sensor is defined as:

$$\text{EMN}(f) = \frac{e_{\Sigma}(f)}{S_y}$$

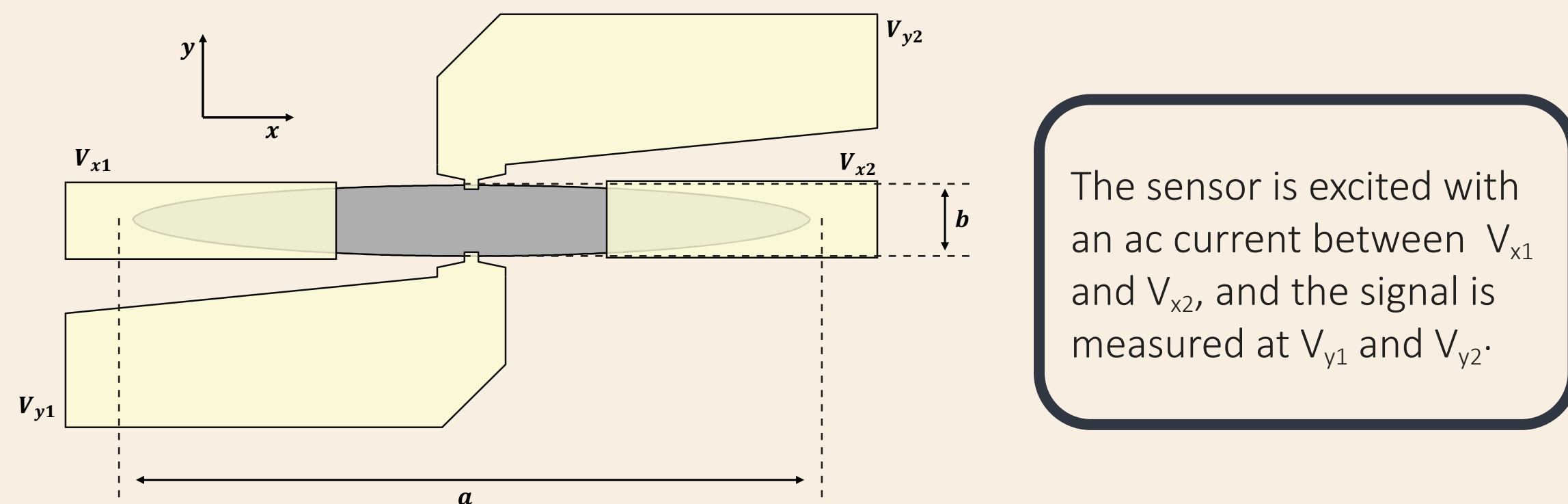
The total noise spectral density (e_{Σ}) has three main components: $1/f$ noise, thermal noise (both originating from the sensor), and preamplifier noise. Namely:

$$e_{\Sigma}(f) = \sqrt{e_{1/f}^2 + e_T^2 + e_{\text{amp}}^2}$$

$1/f$ noise dominates at low frequencies, while thermal (white) noise prevails at high frequencies.

Design and Materials

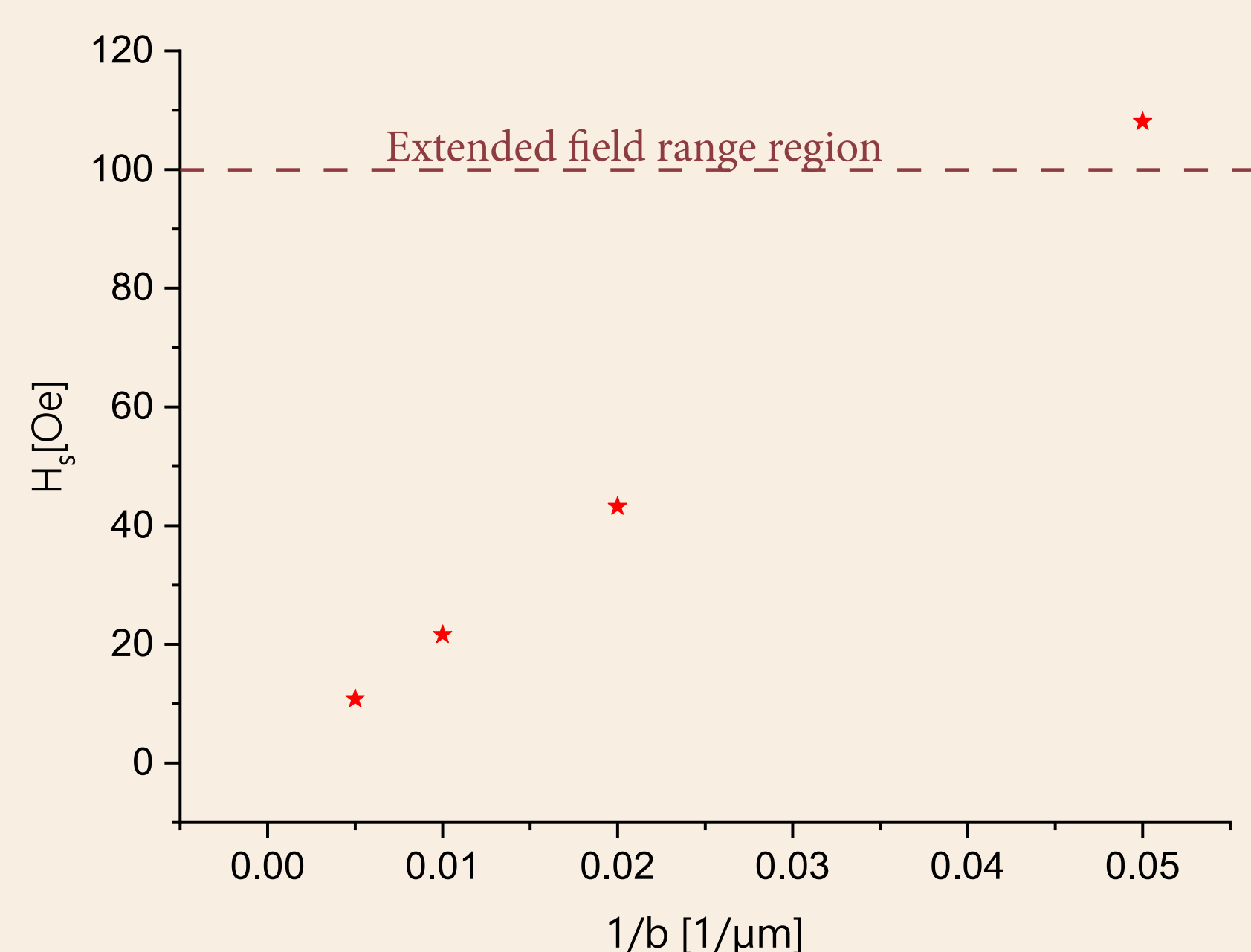
Permalloy (Py, $\text{Ni}_{80}\text{Fe}_{20}$) is used as the ferromagnetic layer for its high PHE sensitivity and low coercive field. Tantalum (Ta) acts as a seeding layer to improve crystallographic ordering and reduce coercivity, while also serving as a capping layer to protect the Py from oxidation.



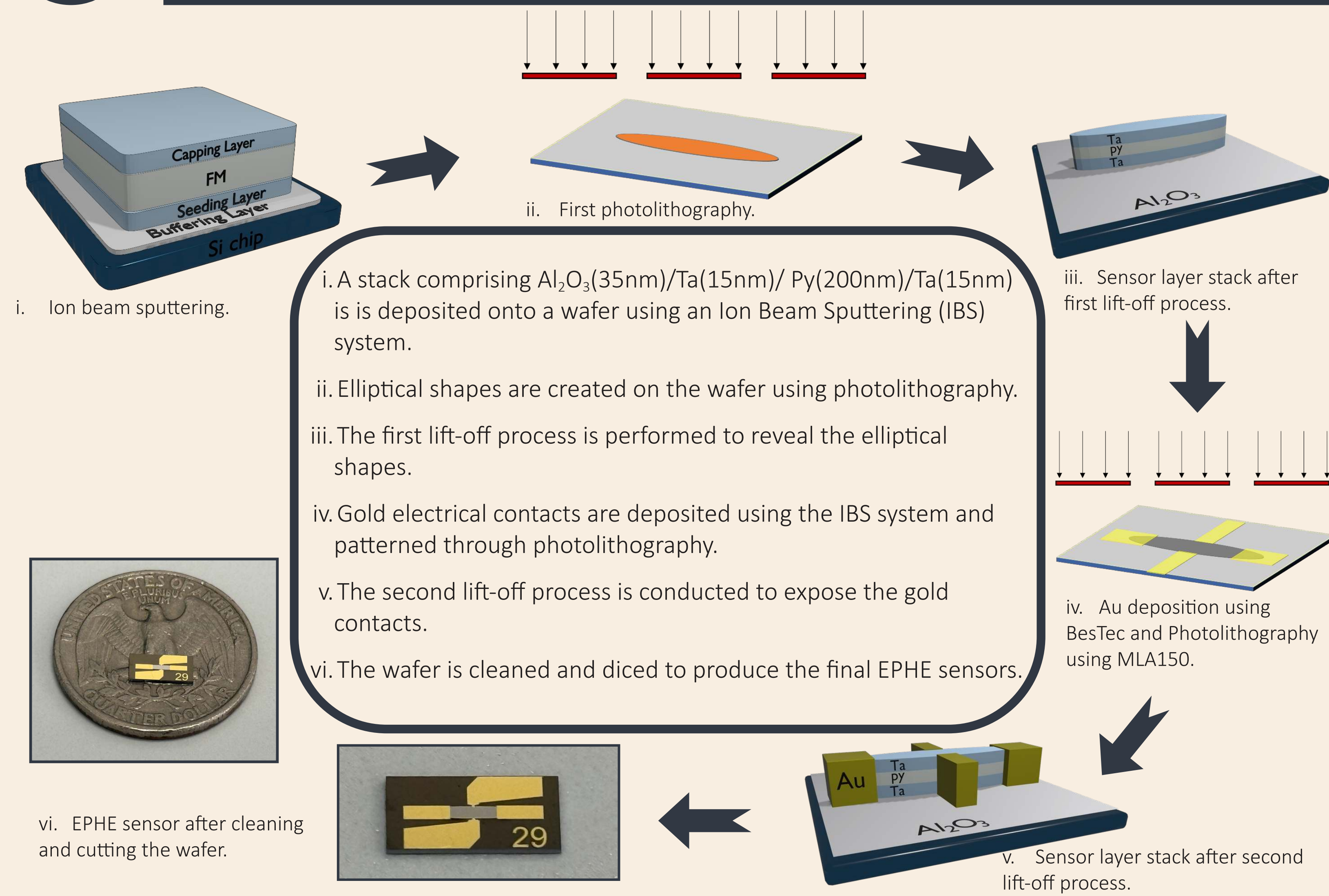
A Novel EPHE Sensor with Extended Field Range

Using the dependence of shape anisotropy on t and b , theoretical calculations show that sensors with a hard axis length of 20 microns reach shape anisotropy fields exceeding 100 Oe.

Consequently, EPHE sensors were fabricated with a thickness of 200 nm and diverse hard axis lengths, specifically 200, 100, 50, and 20 microns.



3 Fabrication Process



4 Results and Discussion

Table 1 demonstrates that reducing the hard axis dimension (b) while maintaining the a/b ratio extends the field range of the EPHE sensor. At a constant current density, the 20-micron sensor's sensitivity is approximately 100 times lower than the 200-micron sensor, matching theory.

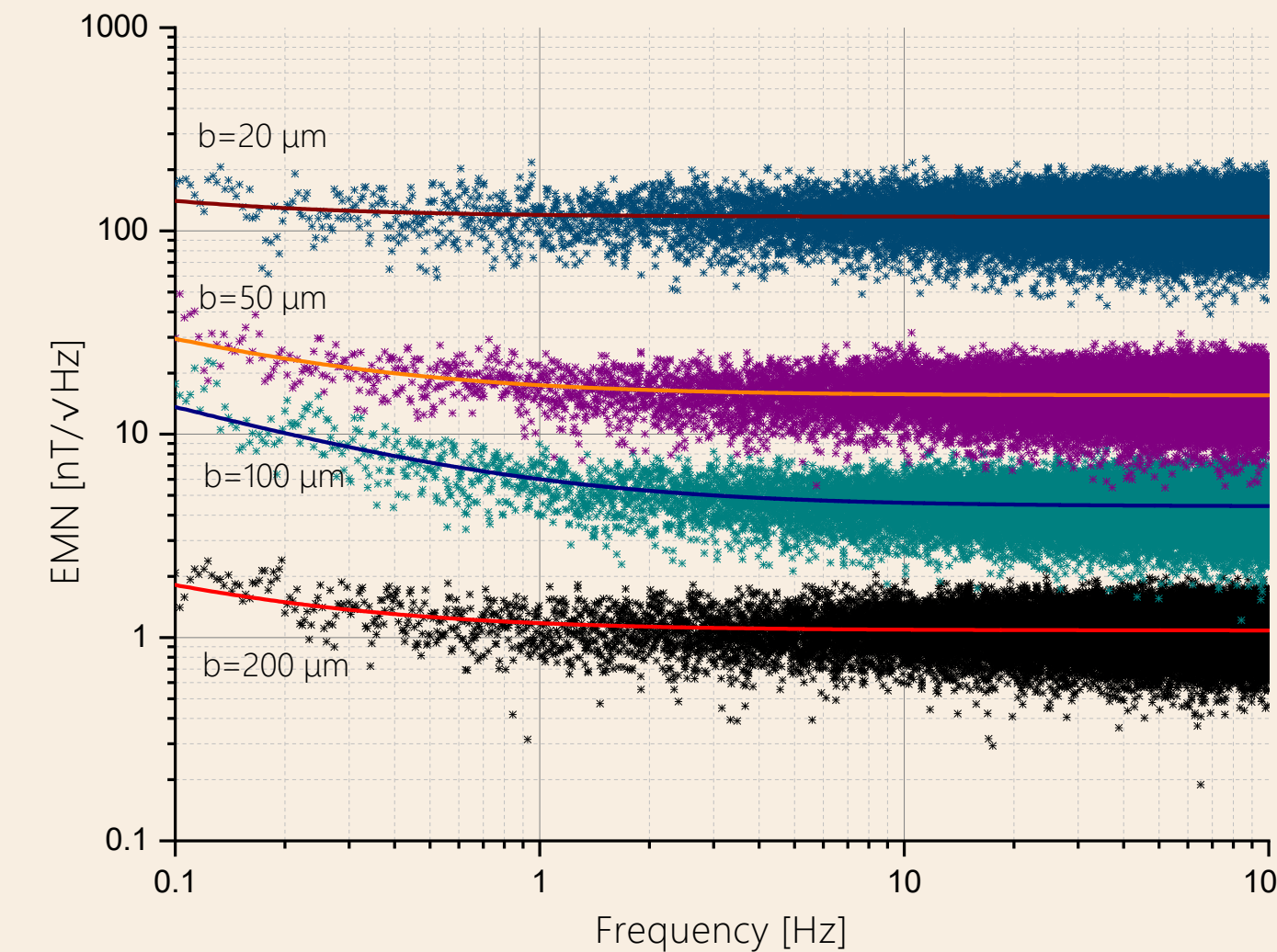


Figure 1. EMN vs. frequency for PHE sensors with varying hard axis (b) values at the same current density.

Figure 2 shows the extended field range of the sensors in response to a magnetic field along the hard axis. The resistivity was measured during both ascending and descending fields and compared to the theoretical fit from the Stoner–Wohlfarth model:

$$R_{\text{PHE}} = \frac{\Delta R_{\text{PHE}}}{H_{\text{eff}}} \cdot H \sqrt{1 - \left(\frac{H}{H_{\text{eff}}}\right)^2}$$

It is evident that although all sensors exhibit non-linear behavior, this behavior can be precisely modeled, which means that they effectively behave as single magnetic domains.

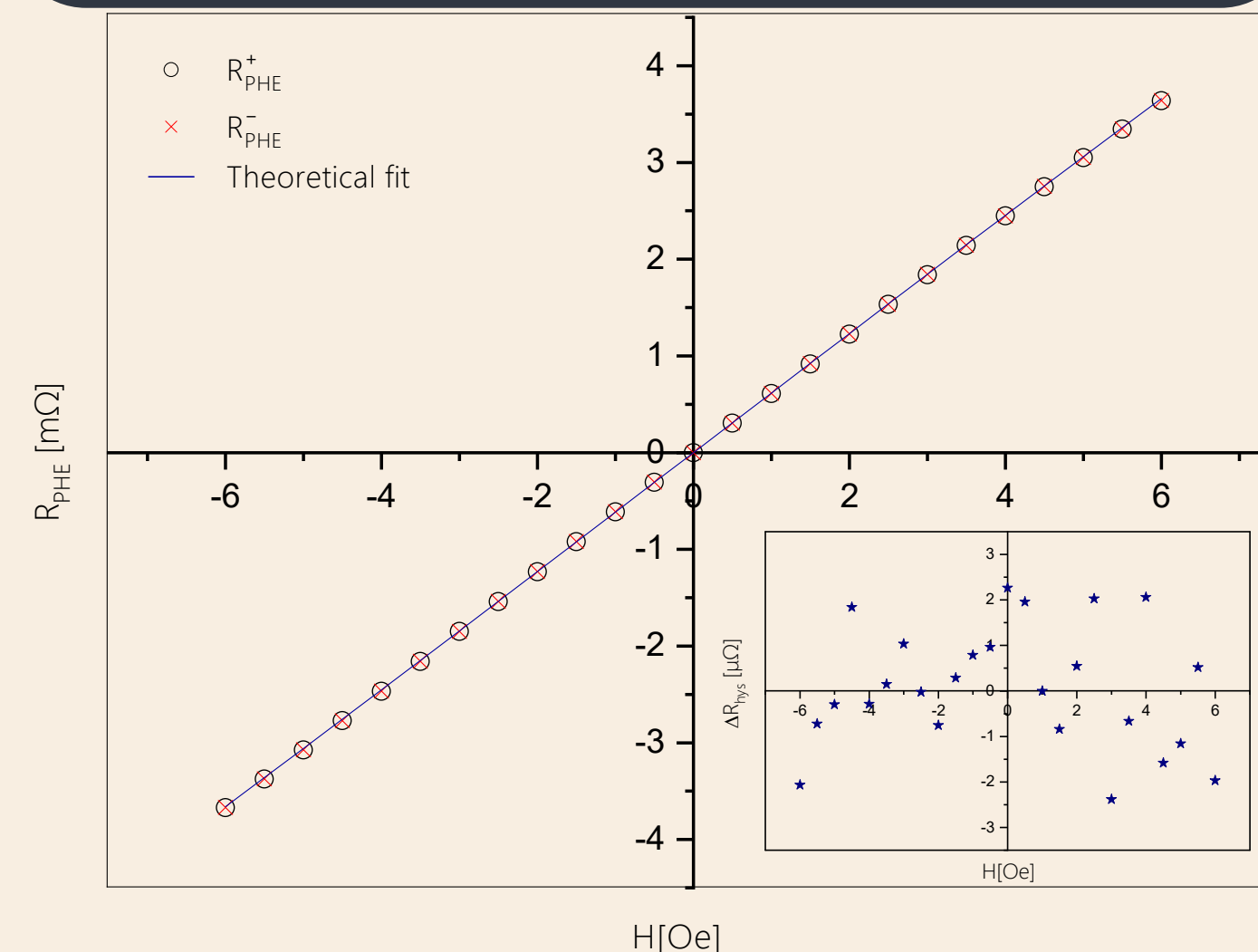


Figure 3. R_{PHE}^+ and R_{PHE}^- vs. applied field for the 50 μm sensor. The inset shows the resistivity difference between decreasing from +14 Oe and increasing from -14 Oe.

b (μm)	I (mA)	H_{eff} (Oe)	S_y (mV/T)	ΔR_{PHE} (m Ω)	R_x (Ω)	R_y (Ω)
20	3	124.8	7.2	29	8.9	35.6
50	7.5	43.5	46	26	7	20.7
100	15	23.8	151.5	25	5.6	14.4
200	30	13.5	642.1	26	5.1	9.8

Figure 1 shows the EMN from 0.1 to 100 Hz for sensors with varying hard axis values. The EMN is fitted using:

$$\text{EMN}(f) = \sqrt{B^2 + \frac{A^2}{f}}$$

where A and B are fitting parameters. At 10 Hz, the EMNs are approximately 1.1, 4.4, 16, and 117 nT/VHz for hard axis values of 200, 100, 50, and 20 microns, respectively.

Doubling the current density results in EMNs of 56 nT/VHz and 7.7 nT/VHz at 10 Hz for the 20-micron and 50-micron sensors, respectively.

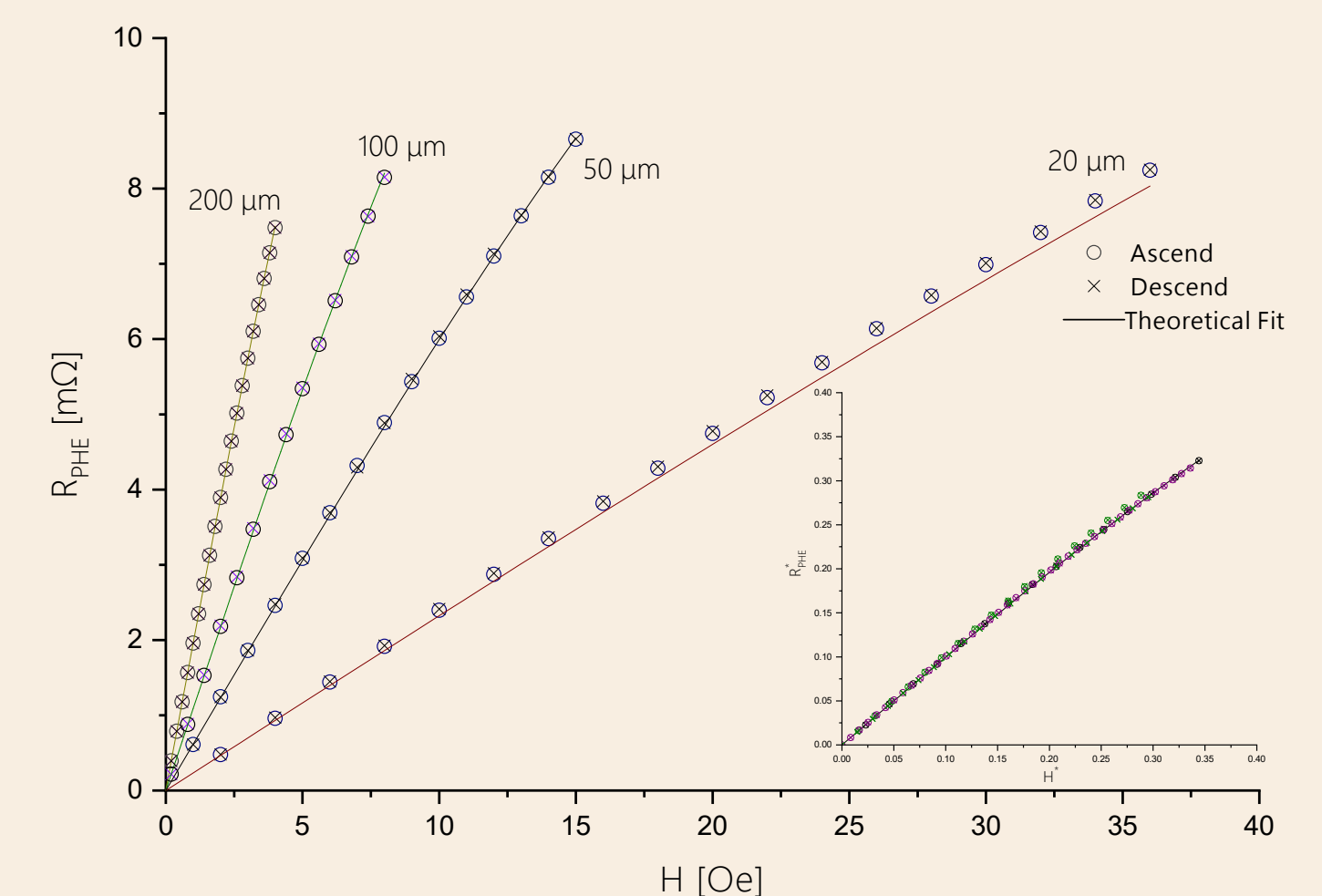


Figure 2. Operational field ranges for sensors with different hard axis lengths. The inset presents scaled data with normalized values.

To evaluate hysteresis for a sensor with $b=50\mu\text{m}$, R_{PHE} was measured in a -6 Oe to $+6$ Oe field range (linearity deviation $< 1\%$) with 0.5 Oe steps.

Measurements were taken by reducing the field from +14 Oe (R_{PHE}^+) and increasing it from -14 Oe (R_{PHE}^-).

Figure 3 shows R_{PHE}^+ and R_{PHE}^- , with the inset displaying $\Delta R_{\text{PHE}} = R_{\text{PHE}}^+ - R_{\text{PHE}}^-$.

Significantly, ΔR_{PHE} changes sign, indicating that the differences are largely unrelated to magnetic hysteresis. Nevertheless, ΔR_{PHE} can still be considered an upper bound for any potential magnetic hysteresis.

5 Conclusions

We demonstrated that extending the field range of EPHE sensors by increasing the ratio of thickness to the short axis significantly enhances their performance. Sensors with anisotropy fields of 12–120 Oe achieved EMNs of 800 pT/VHz to 56 nT/VHz, exhibiting stable single-domain behavior with negligible hysteresis.

These advancements make EPHE sensors promising for precise magnetic sensing in applications requiring extended field ranges, such as automotive and industrial systems.

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